RF Power Field Effect Transistors

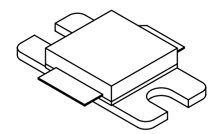
N-Channel Enhancement-Mode Lateral MOSFETs

MRF6S21050LR3
MRF6S21050LSR3

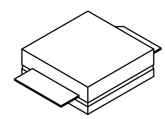
Designed for W-CDMA base station applications with frequencies from 2110 to 2170 MHz. Suitable for TDMA, CDMA and multicarrier amplifier applications. To be used in Class AB for PCN-PCS/cellular radio and WLL applications.

- Typical 2-carrier W-CDMA Performance: V_{DD} = 28 Volts, I_{DQ} = 450 mA, P_{out} = 11.5 Watts Avg., Full Frequency Band, Channel Bandwidth = 3.84 MHz, PAR = 8.5 dB @ 0.01% Probability on CCDF.
  Power Gain — 16 dB
  Drain Efficiency — 27.7%
  IM3 @ 10 MHz Offset — -37 dBc @ 3.84 MHz Channel Bandwidth
  ACPR @ 5 MHz Offset — -40 dBc @ 3.84 MHz Channel Bandwidth
- Capable of Handling 10:1 VSWR, @ 28 Vdc, 2140 MHz, 50 Watts CW Output Power
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Internally Matched, Controlled Q, for Ease of Use
- Qualified Up to a Maximum of 32 V_{DD} Operation
- Integrated ESD Protection
- Designed for Lower Memory Effects and Wide Instantaneous Bandwidth Applications
- Low Gold Plating Thickness on Leads, 40μ″ Nominal.
- In Tape and Reel. R3 Suffix = 250 Units per 32 mm, 13 inch Reel.

2170 MHz, 11.5 W AVG., 28 V
2 x W-CDMA
LATERAL N-CHANNEL
RF POWER MOSFETs



CASE 465E-04, STYLE 1
NI-400
MRF6S21050LR3



CASE 465F-04, STYLE 1
NI-400S
MRF6S21050LSR3

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +68	Vdc
Gate-Source Voltage	V_{GS}	-0.5, +12	Vdc
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	151 0.86	W W/°C
Storage Temperature Range	T_{stg}	- 65 to +150	°C
Operating Junction Temperature	T_J	200	°C
CW Operation	CW	50	W

NOTE - **CAUTION** - MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.

Table 2. Thermal Characteristics

Characteristic	Symbol	Value (1,2)	Unit
Thermal Resistance, Junction to Case Case Temperature 80°C, 50 W CW Case Temperature 76°C, 12 W CW	$R_{\theta JC}$	 1.16 1.28	°C/W

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22-A114)	1C (Minimum)
Machine Model (per EIA/JESD22-A115)	A (Minimum)
Charge Device Model (per JESD22-C101)	III (Minimum)

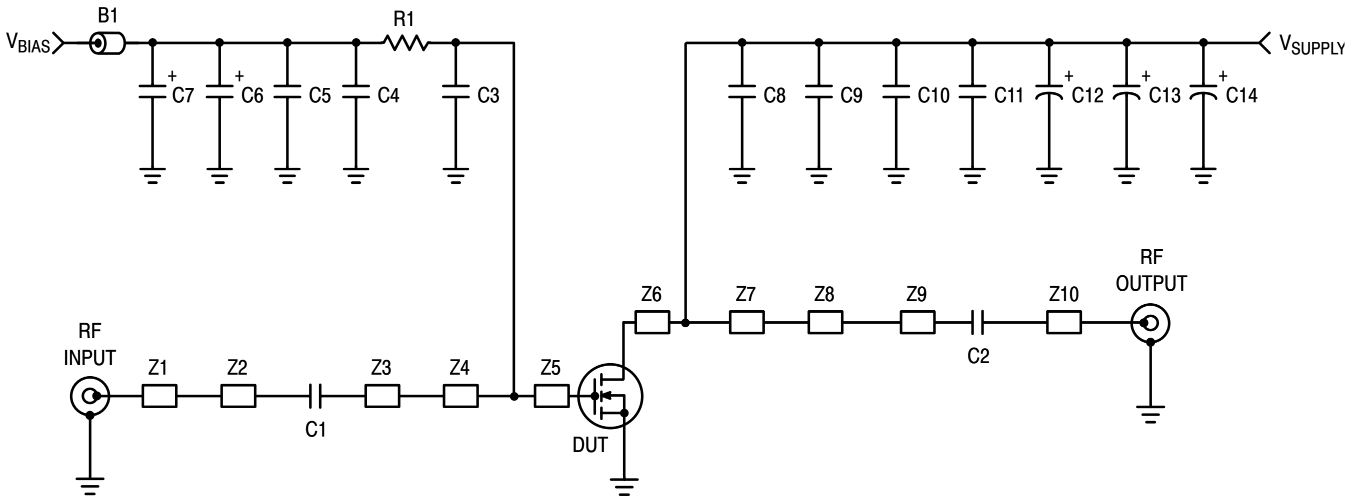
Table 4. Electrical Characteristics (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Off Characteristics					
Zero Gate Voltage Drain Leakage Current (V_{DS} = 68 Vdc, V_{GS} = 0 Vdc)	I_{DSS}	—	—	10	μAdc
Zero Gate Voltage Drain Leakage Current (V_{DS} = 28 Vdc, V_{GS} = 0 Vdc)	I_{DSS}	—	—	1	μAdc
Gate-Source Leakage Current (V_{GS} = 5 Vdc, V_{DS} = 0 Vdc)	I_{GSS}	—	—	1	μAdc
On Characteristics					
Gate Threshold Voltage (V_{DS} = 10 Vdc, I_D = 200 μAdc)	$V_{GS(th)}$	1	2	3	Vdc
Gate Quiescent Voltage (V_{DS} = 28 Vdc, I_D = 450 mAdc)	$V_{GS(Q)}$	2	2.9	4	Vdc
Drain-Source On-Voltage (V_{GS} = 10 Vdc, I_D = 1.1 Adc)	$V_{DS(on)}$	—	0.21	0.3	Vdc
Forward Transconductance (V_{DS} = 10 Vdc, I_D = 1 Adc)	g_{fs}	—	5.3	—	S
Dynamic Characteristics (3)					
Reverse Transfer Capacitance (V_{DS} = 28 Vdc ± 30 mV(rms)ac @ 1 MHz, V_{GS} = 0 Vdc)	C_{rss}	—	0.75	—	pF

Functional Tests (In Freescale Test Fixture, 50 ohm system) V_{DD} = 28 Vdc, I_{DQ} = 450 mA, P_{out} = 11.5 W Avg., f1 = 2112.5 MHz, f2 = 2122.5 MHz and f1 = 2157.5 MHz, f2 = 2167.5 MHz, 2-carrier W-CDMA, 3.84 MHz Channel Bandwidth Carriers. ACPR measured in 3.84 MHz Channel Bandwidth @ ±5 MHz Offset. IM3 measured in 3.84 MHz Bandwidth @ ±10 MHz Offset. PAR = 8.5 dB @ 0.01% Probability on CCDF.

Characteristic	Symbol	Min	Typ	Max	Unit
Power Gain	G_{ps}	15	16	18	dB
Drain Efficiency	η_D	26	27.7	—	%
Intermodulation Distortion	IM3	—	-37	-35	dBc
Adjacent Channel Power Ratio	ACPR	—	-40	-38	dBc
Input Return Loss	IRL	—	-15	-9	dB

1. MTTF calculator available at http://www.freescale.com/rf. Select Tools/Software/Application Software/Calculators to access the MTTF calculators by product.
2. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers.* Go to http://www.freescale.com/rf. Select Documentation/Application Notes - AN1955.
3. Part is internally matched both on input and output.

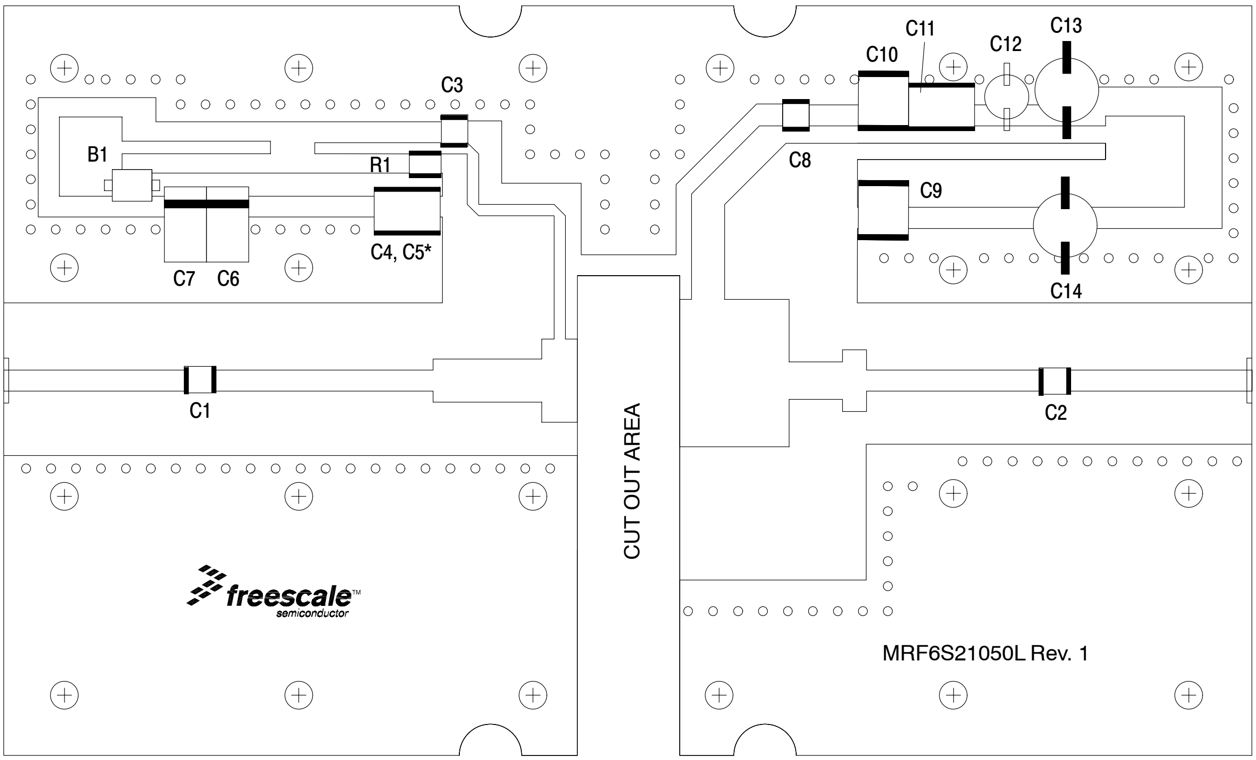


Z1, Z10	0.750″ x 0.084″ Microstrip	Z6	0.113″ x 0.590″ Microstrip
Z2	0.905″ x 0.084″ Microstrip	Z7	0.325″ x 0.590″ Microstrip
Z3	0.435″ x 0.173″ Microstrip	Z8	0.214″ x 0.150″ Microstrip
Z4	0.073″ x 0.333″ Microstrip	Z9	0.723″ x 0.084″ Microstrip
Z5	0.070″ x 0.333″ Microstrip	PCB	Arlon GX-0300-5022, 0.030″, ε_r = 2.5

Figure 1. MRF6S21050LR3(LSR3) Test Circuit Schematic

Table 5. MRF6S21050LR3(LSR3) Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer
B1	Bead, Surface Mount	2743019447	Fair-Rite
C1, C2, C3, C8	6.8 pF Chip Capacitors	100B6R8CP500X	ATC
C4	0.01 μF Chip Capacitor (1825)	C1825C103J1RAC	Kemet
C5, C11	2.2 μF, 50 V Chip Capacitors (1825)	C1825C225J5RAC	Kemet
C6	22 μF, 25 V Tantalum Capacitor	ECS-T1ED226R	Panasonic TE Series
C7	47 μF, 16 V Tantalum Capacitor	T491D476K016AS	Kemet
C9, C10	10 μF, 50 V Chip Capacitors (2220)	GRM55DR61H106KA88B	Murata
C12	47 μF, 50 V Electrolytic Capacitor	MVK50VC47RM8X10TP	Nippon
C13, C14	220 μF, 50 V Electrolytic Capacitors	MVY50VC221MJ10TP	Nippon
R1	3.3 Ω, 1/4 W Chip Resistor (1210)	ERJ-14YJ3R3U	Dale/Vishay



* C4 on bottom, C5 on top.

Figure 2. MRF6S21050LR3(LSR3) Test Circuit Component Layout

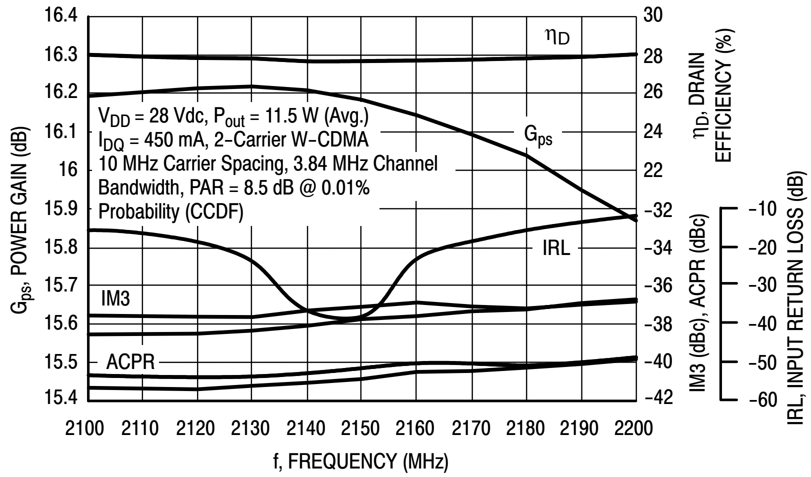


Figure 3. 2-Carrier W-CDMA Broadband Performance @ P_{out} = 11.5 Watts

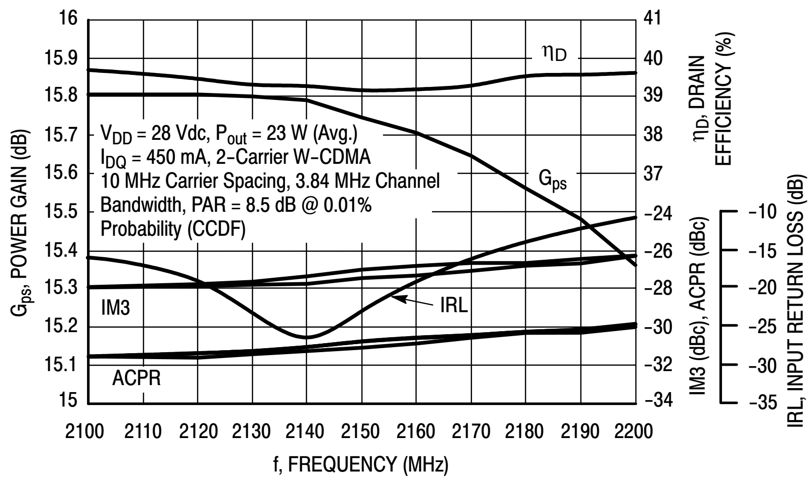


Figure 4. 2-Carrier W-CDMA Broadband Performance @ P_{out} = 23 Watts

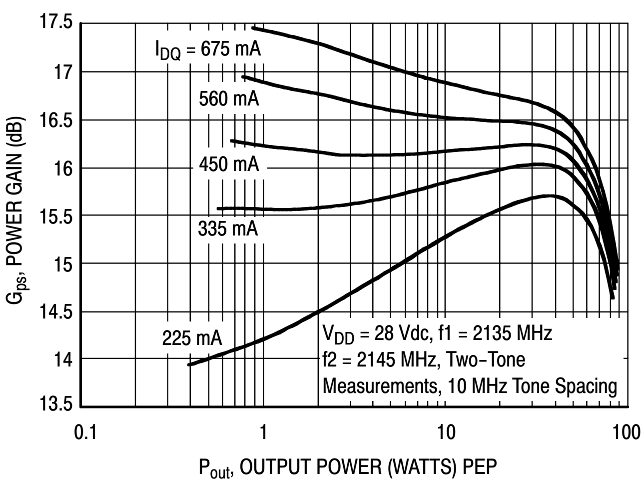


Figure 5. Two-Tone Power Gain versus Output Power

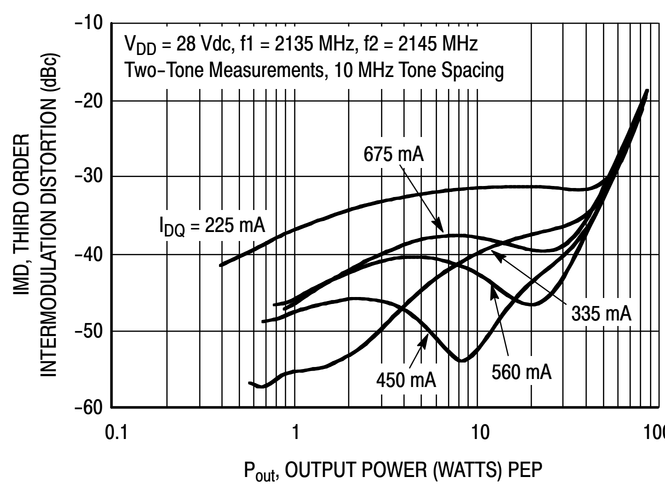


Figure 6. Third Order Intermodulation Distortion versus Output Power

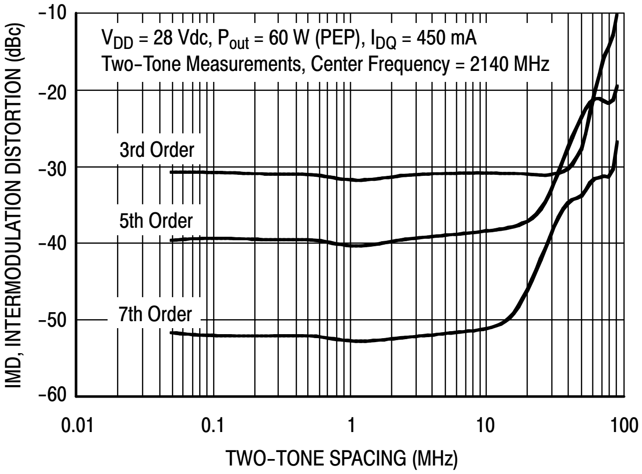


Figure 7. Intermodulation Distortion Products versus Tone Spacing

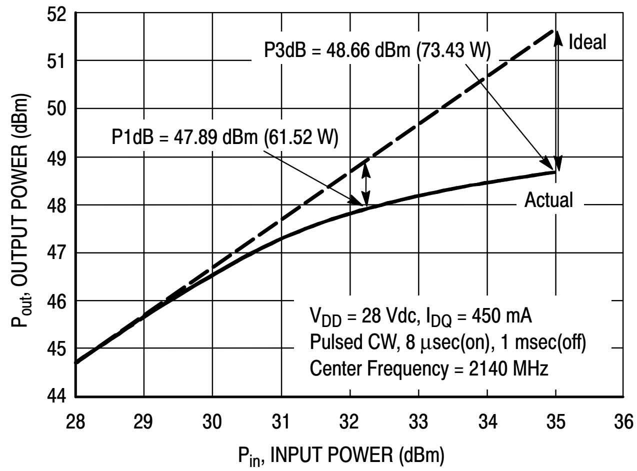


Figure 8. Pulse CW Output Power versus Input Power

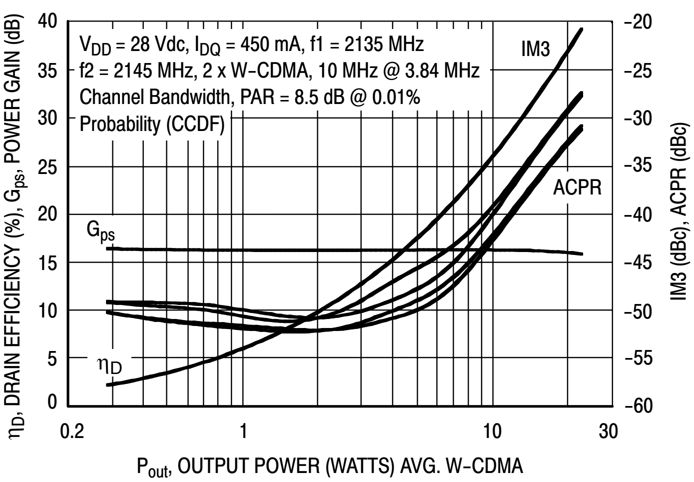


Figure 9. 2-Carrier W-CDMA ACPR, IM3, Power Gain and Drain Efficiency versus Output Power

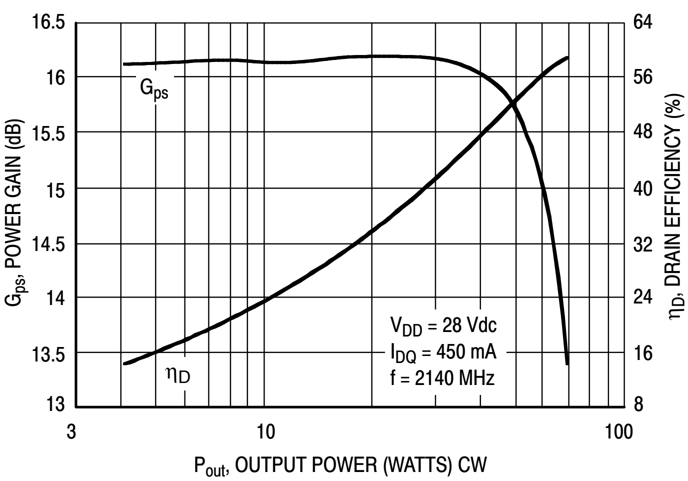


Figure 10. Power Gain and Drain Efficiency versus CW Output Power

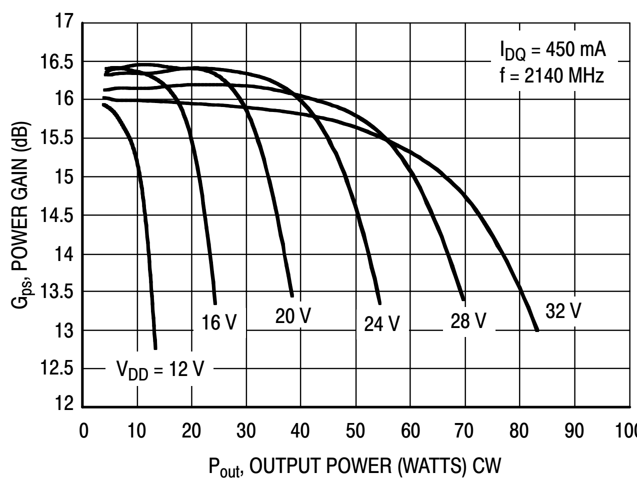
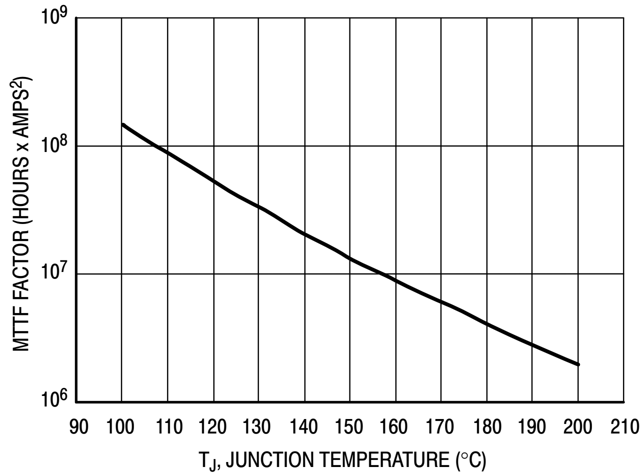


Figure 11. Power Gain versus Output Power

TYPICAL CHARACTERISTICS



This above graph displays calculated MTTF in hours x ampere^2 drain current. Life tests at elevated temperatures have correlated to better than ±10% of the theoretical prediction for metal failure. Divide MTTF factor by I_D^2 for MTTF in a particular application.

Figure 12. MTTF Factor versus Junction Temperature

W-CDMA TEST SIGNAL

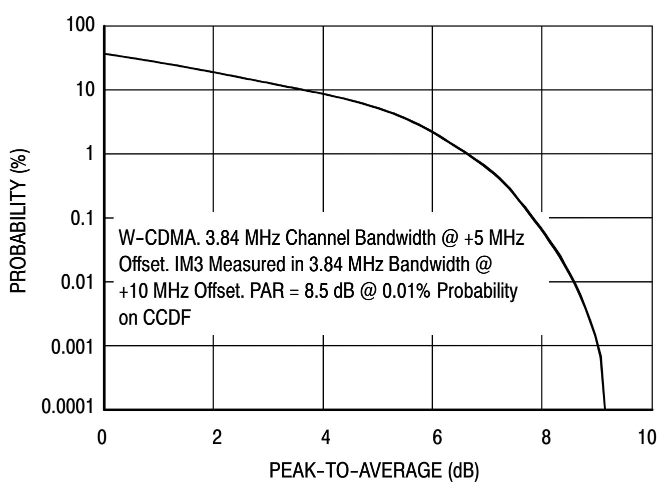


Figure 13. CCDF W-CDMA 3GPP, Test Model 1, 64 DPCH, 67% Clipping, Single-Carrier Test Signal

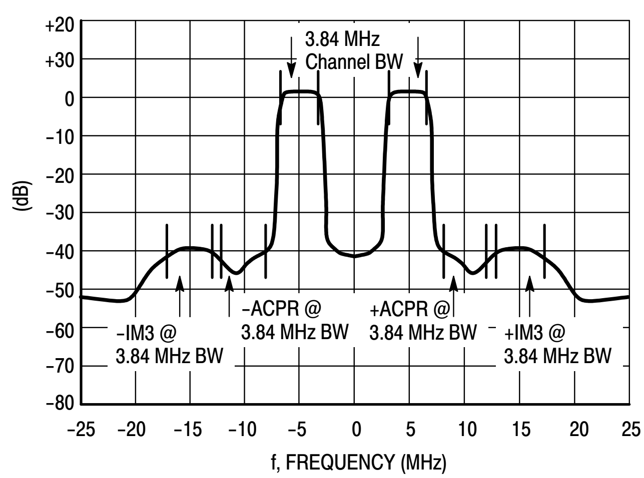
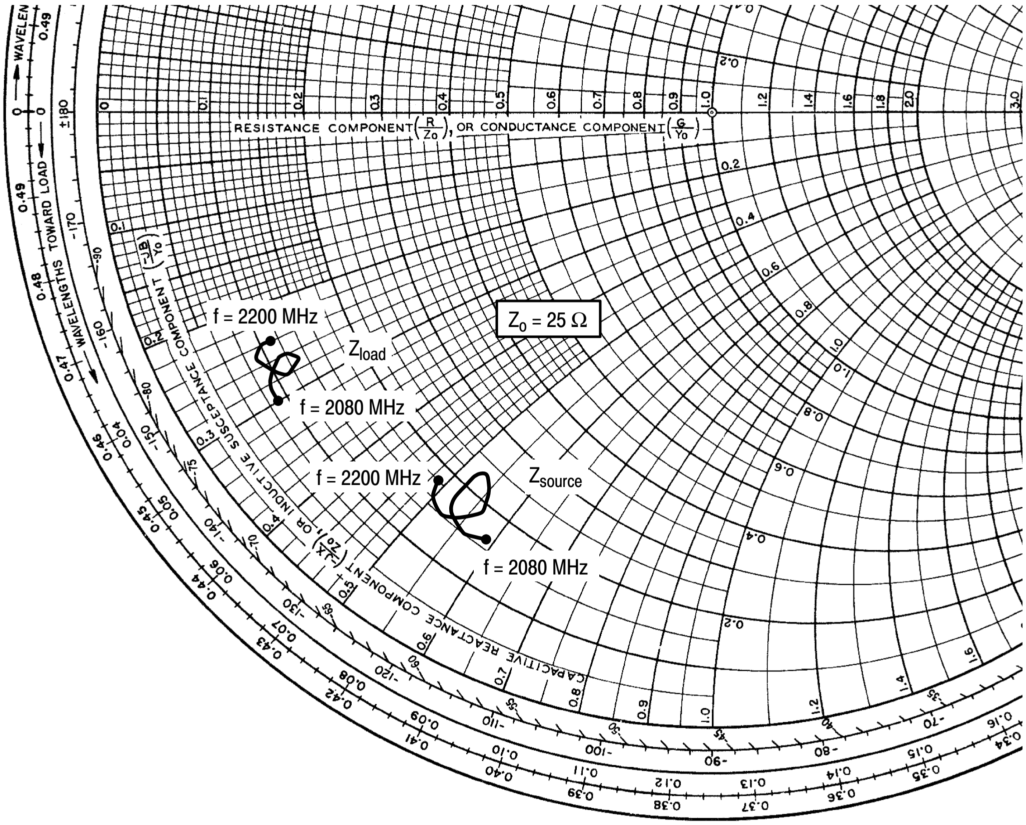


Figure 14. 2-Carrier W-CDMA Spectrum



V_{DD} = 28 Vdc, I_{DQ} = 450 mA, P_{out} = 11.5 W Avg.

f MHz	Z_{source} Ω	Z_{load} Ω
2080	4.09 - j14.65	2.36 - j7.52
2090	3.74 - j13.95	2.25 - j7.11
2100	3.95 - j13.36	2.40 - j6.78
2110	4.44 - j13.00	2.68 - j6.59
2120	5.03 - j12.89	2.99 - j6.52
2130	5.55 - j13.05	3.26 - j6.64
2140	5.76 - j13.26	3.32 - j6.68
2150	5.57 - j13.70	3.20 - j6.87
2160	4.86 - j13.92	2.82 - j6.93
2170	4.04 - j13.61	2.44 - j6.70
2180	3.69 - j12.91	2.33 - j6.29
2190	3.91 - j12.44	2.49 - j6.05
2200	4.41 - j12.32	2.77 - j5.96

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

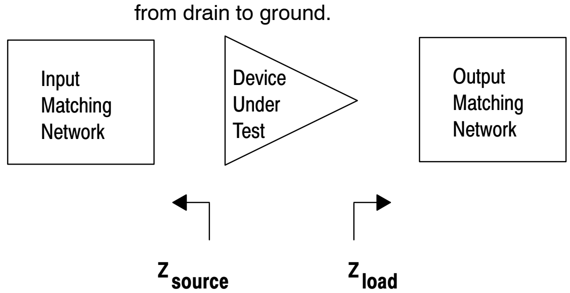
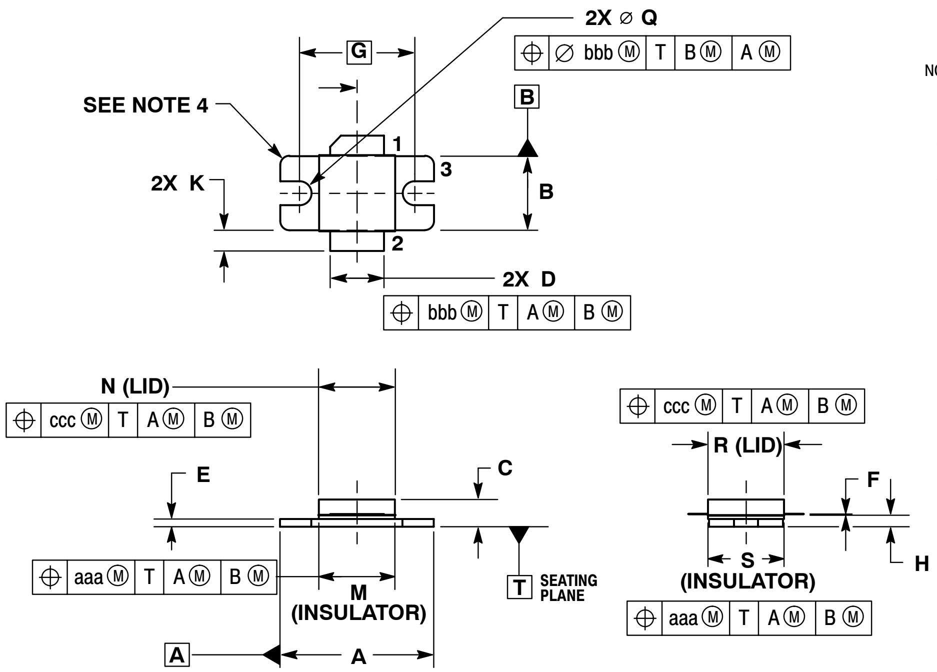


Figure 15. Series Equivalent Source and Load Impedance

NOTES

NOTES

PACKAGE DIMENSIONS

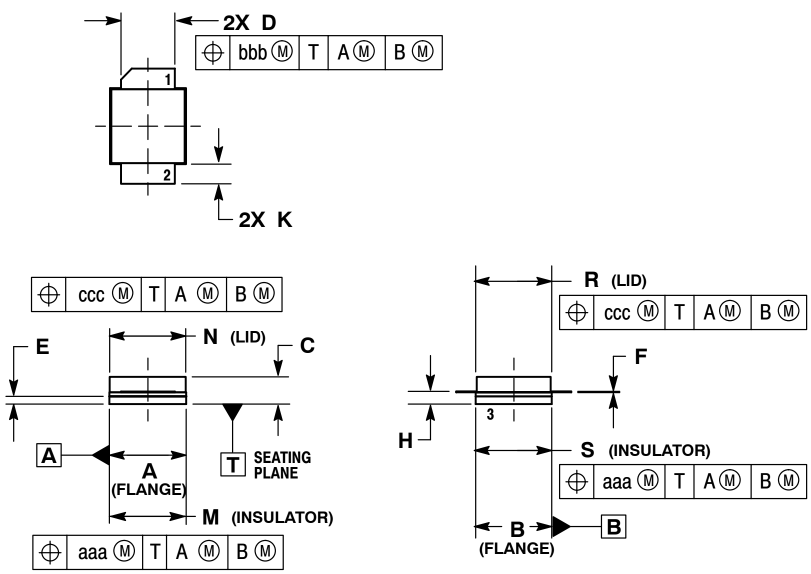


NOTES:
1. CONTROLLING DIMENSION: INCH.
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
3. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.
4. INFORMATION ONLY: CORNER BREAK (4X) TO BE .060±.005 (1.52±0.13) RADIUS OR .06±.005 (1.52±0.13) x 45° CHAMFER.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	.795	.805	20.19	20.44
B	.380	.390	9.65	9.9
C	.125	.163	3.17	4.14
D	.275	.285	6.98	7.24
E	.035	.045	0.89	1.14
F	.004	.006	0.10	0.15
G	.600 BSC		15.24 BSC	
H	.057	.067	1.45	1.7
K	.092	.122	2.33	3.1
M	.395	.405	10	10.3
N	.395	.405	10	10.3
Q	∅.120	∅.130	∅3.05	∅3.3
R	.395	.405	10	10.3
S	.395	.405	10	10.3
aaa	.005 BSC		0.127 BSC	
bbb	.010 BSC		0.254 BSC	
ccc	.015 BSC		0.381 BSC	

STYLE 1:
PIN 1. DRAIN
2. GATE
3. SOURCE

CASE 465E-04
ISSUE E
NI-400
MRF6S21050LR3



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	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
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C	.125	.163	3.18	4.14
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E	.035	.045	0.89	1.14
F	.004	.006	0.10	0.15
H	.057	.067	1.45	1.70
K	.092	.122	2.34	3.10
M	.395	.405	10.03	10.29
N	.395	.405	10.03	10.29
R	.395	.405	10.03	10.29
S	.395	.405	10.03	10.29
aaa	.005 REF		0.127 REF	
bbb	.010 REF		0.254 REF	
ccc	.015 REF		0.38 REF	

STYLE 1:
PIN 1. DRAIN
2. GATE
3. SOURCE

CASE 465F-04
ISSUE C
NI-400S
MRF6S21050LSR3

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